

I. LISTA CELOR MAI RELEVANTE LUCRARI

1. **Cristian Ravariu**, Cătălin Pârvulescu, Elena Manea, Adrian Dinescu, Raluca Gavrila, Munizer Purica, Vijay Arora, "Manufacturing of a Nothing On Insulator Nano-Structure with two Cr/Au Nanowires Separated by 18 nm Air Gap", **Nanotechnology** (IOP Journal), **Q1 zona Rosie** IF=3.39, (Phys. Appl), ISSN: 0957-4484, accepted Feb. 2020.
2. **Cristian Ravariu**, Daniela Istrati, Dan Mihaiescu, Alina Morosan, Bogdan Purcareanu, Rodica Cristescu, Roxana Trusca, Bogdan Vasile, *Solution for green organic thin film transistors: Fe_3O_4 nano-core with PABA external shell as p-type film*, **Journal of Materials Science - Materials in Electronics** (Springer Journal), vol31, no.4, pp. 3063-3073. (ISSN: 0957-4522 (Print) 1573-482X (Online)), **Q2-zona Galbena** IF=2, DOI: 10.1007/s10854-019-02851-3, Accepted 31 Dec 2019, Published 11 Ian 2020.
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3. V.M. Placinta, L.N. Cojocariu and **C. Ravariu**, *Proton-induced radiation effects in the I/O blocks of an SRAM-based FPGA*, **Journal of Instrumentation** (IOP Journal), 2019 JINST, vol 14, no. 10, T10001. **Q3** IF=1.38. DOI: <https://doi.org/10.1088/1748-0221/14/10/T10001>, pp. 1-9.ISSN 1748-0221.
4. **Ravariu C.**, Manea E., Babarada F., Ursutiu D., Mihaiescu D., Popescu A., "Organic Compounds Integrated on Nanostructured Materials for Biomedical Applications", Chapter 2 at section Biomedical Engineering in **Springer book: Smart Industry & Smart Education**. Editors: Auer M., Langmann R., vol 47. Springer, Cham, Jan 2019, pp 489-497, WOS:000455197300055, DOI:10.1007/978-3-319-95678-7_55, Publisher Name - Springer, Print ISBN 978-3-319-95677-0, Online ISBN 978-3-319-95678-7, ISSN: 2367-3370.
5. **Cristian RAVARIU**, Nicu BIZON, Elena MANEA, Florin BABARADA, Cătălin PÂRVULESCU , Dan Eduard MIHAIESCU, Maria STANCA, Chapter 12 " PV Microgrids Efficiency: From Nanomaterials and Semiconductor Polymer Technologies for PV Cells to Global MPPT Control for PV Arrays " in **Springer Book "Microgrid Architectures, Control and Protection Methods"**, Series Title "Power Systems", Editors: Naser Mahdavi Tabatabaei, Ersan Kabalci, Nicu Bizon, pp. 289-325, July 2019, Print ISBN 978-3-030-23722-6. **Online ISBN** 978-3-030-23723-3, Springer Nature Switzerland.
6. **C. Ravariu**, *Vacuum nano-triode in Nothing-On-Insulator configuration working in Terahertz domain*, **IEEE Journal of the Electron Devices Society**, (IEEE Journal) vol. 6, no. 1, 2018, pp. 1115-1123, DOI 10.1109/JEDS.2018.2868465, Print ISSN: 2168-6734, **Q2-zona Galbena** IF=2.69, WOS:000445354800001 din sept 2018, Publication in IEEE: 03 Sept. 2018. WOS:000445354800001
7. **C. Ravariu**, *Gate Swing Improving for the Nothing On Insulator Transistor in Weak Tunneling*, **IEEE Transactions on Nanotechnology** (IEEE Journal), 2017, Vol. 16, issue 6, pp. 1115 - 1121, **Q2-zona Galbena** IF=2, DOI: 10.1109/TNANO.2017.2764802, unde este mentionat cu contributie totala TFTNANOEL. WOS:000415707200029, ISSN: 1536-125X, Premiere cu numarul de inregistrare PN-III-P1-1.1-PRECISI-2018-21588.
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II. TEZA DE DOCTORAT (T)

T1. **Cristian Ravariu.** *Structuri integrate pe substraturi izolate dielectric*, Biblioteca centrală a Universității Politehnica din București, 2001, coordonator Prof. dr. ing. Adrian Rusu.
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Cb.1. Cristian Ravariu. *Biodispozitive electronice: de la nanostructuri la aplicații medicale*, Editura Politehnica Press, ISBN 978-606-515-071-3, București, 2010, pag. 1-232.

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Categories / Classification ISI :Research Areas:Engineering, **Web of Science Categories:**Engineering, Biomedical

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VIII. BREVETE DE INVENTIE (B) SI ALTE TITLURI (A) DE PROPRIETATE INDUSTRIALĂ SI INTELECTUALĂ

B.1. Cristian Ravariu. Tranzistor cu efect de câmp de tip cavitate pe izolator și procedeu de realizare al acestuia, Brevet OSIM nr. A/01130 din 18.11.2010. A trecut toate etapele de examinare, apoi în Apr. 2013 a fost trimisă Hotărârea de accordare a brevetului, în Iun. 2013 au fost plătite toate taxele, iar în Sept. 2013 se așteaptă diploma brevet, inclus din Aug. 2013 in baza ISI cu Patent Number: RO126811-A0.

Engl. C. Ravariu, "Field effect transistors with a cavity on insulator, NOI and a-NOI," Romanian Patent Number: RO126811-A0, OSIM, Aug. 2013.

B.2. Florin Babarada, Elena Manea, **Cristian Ravariu**. Procedeu de fabricație pe siliciu a dispozitivelor pentru detecția și caracterizarea moleculelor biologice încărcate cu sarcină electrică; Brevet depus la OSIM, cu nr. înregistrare A/01023 din 07.12.2009, a trecut de etapele de publicare, examinare, inclus din Aug. 2013 in baza ISI cu Patent Number: RO126615-A2 și Derwent Primary Accession Number: 2011-Q12664 [01] in baza ISI, cu Diploma de Brevet de inventie nr. 126615 din 27.11.2015, publicat in Buletinul oficial de proprietate industrială - sectiunea inventii nr. 11/2015 OSIM, Patent Number(s): RO126615-A2 ; RO126615-B1, Derwent Primary Accession Number: 2011-Q12664 [78]. Diploma de Brevet de inventie nr. 126615 din 27.11.2015, publicat in Buletinul oficial de proprietate industrială BOPI nr. 11 - sectiunea inventii nr. 11/2015 OSIM. la OSIM - BOPI 11, publ in **27/11/2015**.

Engl. Florin Babarada, Elena Manea, **Cristian Ravariu**. Process for manufacturing, on silicon, the devices for detecting and characterizing the electrically charged biological molecules, Patent Number(s): RO126615-A2 ; RO126615-B1, 27 Nov 2015, OSIM Romanian agency.

B.3. C. Ravariu, Tranzistoare cu filme organice p/n suprapuse pentru aplicații biomimetice și industriale, Brevet depus la OSIM, cu nr. înregistrare A/00021 din 12.01.2016, a trecut de etapele de publicare.

En: C. Ravariu: Transistors with p/n overlap films for biomimetic and industrial applications, Registered at OSIM Romanian Agency no. A/00021 from 12.01.2016, pass in second stage from Apr. 2016.

IX. CONTRACTE CERCETARE

Proiecte câștigate la care Cristian Ravariu a fost director de proiect, PD

PD.1. Contract nr. 6111/2000, Modelarea conduceției prin tranzistoare SOI-MOSFET cu profile uniforme și neuniforme ale concentrației de impurități în film, **Grant T**, TEMA A.56, 2 ani, volum finanțare: 50 000 000 ROL, finanțatorul - A.N.S.T.I, derulare 2000-2001.

PD.2. Contract CNCSIS, Dispozitive MOS cu poartă mobilă pentru circuite de Telecomunicații, **Grant At** cu Tema nr. 21, cod 114, finanțator CNCSIS, volum finanțare 86 000 000 ROL, derulare 2002-2004.

PD.3. Contract CNCSIS, Sisteme de caracterizare electrică nedistructivă pentru materiale SOI nanostructurate, **Grant A**, Tema nr. 25, Cod 63, finanțator CNCSIS, volum finanțare: 98 900 RON, derulare 2006-2007.

PD.4. Contract nr. 12-095/ 01.10.2008, (BioFET), Tranzistoare BioFET pentru bioanalize personalizate și estimări funcționale celulare, Programul Proiecte Complexe **PNII Parteneriate**, comisia 1 (Tehnologia informației și comunicații), finanțator UEFISCDI, volum finanțare per proiect: 810 582 RON, Derulare: 01.10.2008 – 30.09.2011.

PD.5. Contract nr. 62-063/ 01.10.2008, (ElectroCel), Tehnologie neinvazivă de caracterizare funcțională a masei beta celulare cu biodispozitive electronice neconvenționale, Programul Proiecte Complexe **PNII Parteneriate**, comisia 6 (Biotehnologii), finanțator UEFISCDI, volum finanțare per proiect: 803 149 RON, Derulare: 01.10.2008 – 30.09.2011.

V. proiecte : PCE si PED.

PD6. Cristian Ravariu - Director de Proiect, "Nano-tranzistoare cu filme subtiri implementate prin nanotehnologii și tehnologii organice la temperatură camerei", PROGRAMUL PNIII: P4 - Cercetare Fundamentală și de Frontieră, Proiecte de Cercetare Exploratorie - PCE, Acronim: TFTNANOEL, Contract: nr. 4/2017, Cod proiect la depunere: PN-III-P4-ID-PCE-2016-0480, înregistrat la UEFISCDI nr. 254/03.08.2017, nr. int. EL081702, suma angajată: 850.000Lei, derulare 17.iulie 2017-31 Dec. 2019.

PD.7. Cristian Ravariu - Director de Proiect, "Realizare demonstrator în tehnologia planară de tranzistor cu tunelare a izolatorilor ultrasubtiri - ca promotor al unei serii de nano-dispozitive și evidențierea utilitatii în industrie", PROGRAMUL PNIII: P2 - Cresterea competitivității economiei românești prin cercetare, dezvoltare și inovare, **TIP PROIECT:** Proiect Experimental-Demonstrativ - PED, **Acronim:** DEMOTUN, Contract: nr. 205PED/2017, Cod proiect la depunere: PN-III-P2-2.1-PED-2016-0427, înregistrat la UEFISCDI nr. PN3-P2-864/11.09.2017, nr. int. EL081704, suma angajată: 475.000Lei, derulare 17.08.2017-31 Dec. 2018.

Proiecte POSDRU, PO

PO.1. Proiectul **POSDRU/89/1.5/S/62557** - Domeniul Major de Interventie 1.5.: "**Programe Postdoctorale**" - Proiectul Excel - Excelentă în cercetare prin programe postdoctorale în domenii prioritare ale societății bazate pe cunoaștere (EXCEL ID 62557), tema individuală: Structuri SOI generalizate pentru nanotranzistoare și biodispozitive, finanțator - Autoritatea de Management al Programului Sectorial Dezvoltarea Resurselor Umane AM POSDRU, Funcția - **Conf. dr. ing. Cristian Ravariu - Postdoctorand**, Domeniul Electronică și Telecomunicații, Derulare 15 iun. 2010 - 30 apr. 2013.

PO.2. Proiectul POSDRU/87/1.3/S/61397 "Rețea Națională de Formare CONtinuă a CadrelOR Didactice din Învățământul Preuniversitar Profesional și Tehnic – CONCORD", Funcția **Conf. dr. ing. Cristian RAVARIU - Expert pe termen scurt** (3 luni / an) – Expert formare la Modulul 1 (Proelectric 1), la direcția Opțional 2, curs 3 Programul SPICE de simulare a circuitelor electronice. Derulare: 2011-2013.

Proiecte internaționale ca participant, PI

PI.1. Director contract: Adrian Rusu, participant: **C. Ravariu**, Modele avansate pentru tranzistoare bipolare și MOS submicronice, **Contract C.35 cu Banca Mondială**, București, România, derulare 1999-2002.

PI.2. Director contract: Adrian Rusu, participant: **C. Ravariu**, Dispozitive circuite și microsisteme electronice, **Contract D107 cu Banca Mondială**, București, România, derulare 1999-2001.

PI.3. Director contract: A. M. Ionescu (Swiss), participant: **C. Ravariu**, Low power electrostatic silicon on sapphire RF switches for telecom applications, Contract cod ESSOS, Wildhainweg 20 CH-3001. Proiect internațional finanțat **Swiss National Science Foundation**, Ecole Politehnique Federale de Lausanne și Universitatea Politehnica București, România, derulare între 2000-2003.

Proiecte Nationale ca participant, PP

PP.1. Contract nr. 32 – 158 / 01.10.2008, Tehnologii cu grad scăzut de poluare pentru obținerea celulelor fotovoltaice utilizând materiale oxidice nanostructurate, (NANOMATCELL), comisia 3 (mediu), Programul Proiecte Complexe **PNII Parteneriate**, Director : Elena Manea, C. Ravariu: participant, UPB – Partener P1, derulare 2008-2011.

PP.2. Contract nr. 12128 / 01.10.2008, Procese și dispozitive pe bază de straturi subțiri oxidice și polimerice pentru Electronică și OptoElectronică transparentă, (ELOTRANSPI), comisia 1 (IT), Programul Proiecte Complexe **PNII Parteneriate**, Director: Purica Munizer, C. Ravariu: participant, UPB – Partener P1, derulare 2008-2011.

PP.3. Contract nr. 717 / Cod CNCSIS 449, O nouă categorie de dispozitive electronice și circuitele corespunzătoare, Programul **PN2 Idei**, finanțator CNCSIS, Director: A. Rusu, C. Ravariu - participant, derulare 2009-2011.

PP.4. Contract 75, ENIAC RTN-NANOEL, Technology Network for Romania integration in the NANOElectronics european platform, **CEEX Project**, Director Contract: Dan Dascalu, participant: C. Ravariu, finanțator ANCS, (IMT-coord., UPB-partener P1), derulare 2006-2009.

PP.5. Contract CEEX, IMT-coord., UPB-partener, Microstructuri de senzori și actuatori destinate micropozitionării și micromanipulării – mecanice și biologice - MEMSAS (Microgripper), **CEEX Project**, Director Contract: Raluca Muller, participant: C. Ravariu, derulare 2006-2008.

PP.6. Contract 167/2003, Studiul interacțiunii electro-mecanice în dispozitive funcționale MOS, **Grant al Academiei Române**, Director de contract: Dragos Dobrescu, participant C. Ravariu, proiect GAR 128/2003, contract cu UPB nr. 15.03. 08, București, derulare 2003-2004.

PP.7. Contract 40528/5.11.2003, Caracterizarea electrică avansată a dispozitivelor funcționale MOS, Director de contract: Dragos Dobrescu, participant - C. Ravariu, **Grant CNCSIS tip A**, cod 161, tema 25, contract cu UPB nr. 15.03. 10, București, derulare 2003-2004.

PP.8. Contract nr. 154/03.Aug.2005, Structuri super-panta pentru tehnologii nanometrice, **Grant al Academiei Române**, Director contract: L. Dobrescu, participant: C. Ravariu, cu 1 fază anuală, 2005.

PP.9. Contract nr. 1433/2004, Dispozitive novatoare în nanoelectronică, Director contract: A. Rusu, participant: C. Ravariu, **Grant tip A** CNCSIS, nr. 55, derulare pe 3 ani, 2004-2006.

PP.10. Contract cod CNCSIS 497, O nouă abordare teoretică și experimentală a fenomenelor de conductie electrică în dispozitive semiconductoare, Director contract: A. Rusu, participant: C. Ravariu, **Grant A** nr. 57, derulare pe 3 ani, 2002-2004.

Lista completă de lucrări a Cristian RAVARIU

PP.11. Contract nr. 5076/1999, Tratarea fenomenologică a proceselor de conducție în electronică, pe baza teoremei de conductie electrică neliniară (Rusu), Director contract: Dragoș Dobrescu, participant: C. Ravariu, **Grant A.N.S.T.I.**, Tema A.62, derulare 1999-2000.

PP.12. Contract de cercetare IMT – MCT, Microtehnologii MOS utilizabile în realizarea structurilor de tranzistoare de putere și comutație de înaltă performanță, Director contract: Ovidiu Popa, participant: C. Ravariu, Tema A.12, finantator MCT, derulare 1997-1998.

PP.13. Contract de cercetare IMT – MCT, Caracterizarea dispozitivelor și proceselor tehnologice în fabricația de microsisteme integrate, Director contract: Ovidiu Popa, participant: C. Ravariu, Tema B.1, participant la cele 5 faze ale temei, derulare pe 3 ani, 1994-1996.

PP.14. Contract de cercetare IMT - MCT, Contract nr.2220/1994, Tehnologii pentru microsisteme, Director contract: Adriana Delibaltov, participant: C. Ravariu, Tema A.1, derulare 1994-1995.

PP.15. Contract Nr. 187/2012, New Innovative System for Radiation Safety of Patients Investigated by Radiological Imaging Methods, based on Smart Cards and PKI Infrastructures, SRSPIRIM, comisia 7, Proiect **PNII Parteneriate**, Director: Lidia Dobrescu. Participant: C. Ravariu, derulare 2012-2015, 4 ani, suma angajata total proiect 1 700 000RON, finantator UEFISCDI.

PP16. Contract 35 / 13.08.2014, EL081401. Comisie ICT. Finantator: UEFISCDI. PN2PTPCCA2013-14. "Metoda de diagnostic diferențial al menigitelor prin determinarea profilului de citokine folosind un dispozitiv de măsurare rapidă la punctul de îngrijire (MEDICY)" – partener coordonator de proiect - Inst. Cantacuzino, director de partener UPB - Prof. Dr. Ing. Florin BABARADA, Participant Prof. Cristian Ravariu. Durata 1.10.2014-20.12.2016.

5. Proiect tip resurse umane la UEFISCDI, pentru premierea rezultatelor cercetării, articol își publicat în jurnal plasat în zona galbenă, Cod provizoriu de înregistrare 2012-1674, Project Registration Code: PN-II-RU-PRECISI-2012-6-1177 din 09.10.2012, Cristian Ravariu and Florin Babarada, Modeling And Simulation Of Special Shaped Soil Materials For The Nanodevices Implementation, ISI Journal of Nanomaterials - Hindawi, July 2011, ISSN: 1687-4110, Factor Impact pe 2010 - 1.675, DOI:10.1155/2011/792759 , Article ID 792759, 11 pages, 2011. Premiat, în lista pe oct 2012: Linia 1170, cod PN-II-RU-PRECISI-2012-6-1177. Finantat cu 2000Lei în dec 2012.

27.02. 2020

Prof. dr. ing. Cristian Ravariu